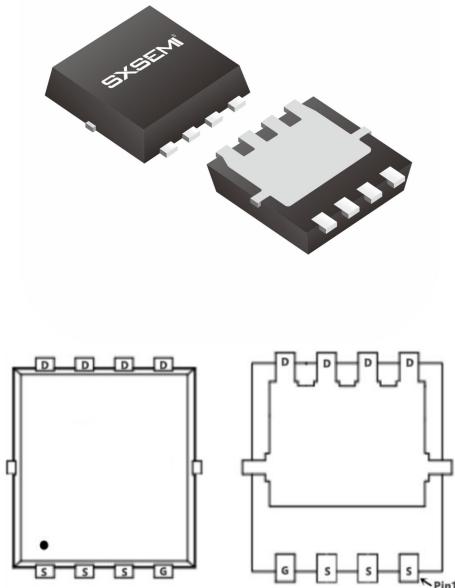


Description

The SX30N02DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

PDFN3*3-8L**General Features**

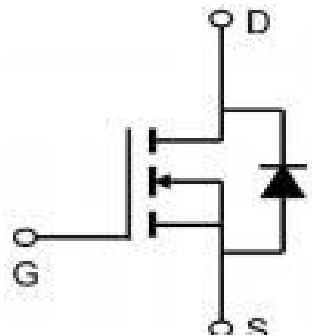
$V_{DS} = 20V$ $I_D = 30A$

$R_{DS(ON)} < 15m\Omega$ @ $V_{GS}=4.5V$

Application

solar road lights

Load switch

**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	13	A
I_{DM}	Pulsed Drain Current ²	50	A
EAS	Single Pulse Avalanche Energy ³	8.1	mJ
I_{AS}	Avalanche Current	12.7	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	20.8	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	6	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	20	22		V
$\Delta BVDSS/\Delta TJ$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.018	---	$\text{V}/^\circ\text{C}$
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.50	0.65	1.0	V
RDS(ON)	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}, I_D=7.6\text{A}$		11	15	$\text{m}\Omega$
RDS(ON)	Static Drain-Source On-Resistance	$V_{GS}=2.5\text{V}, I_D=3.5\text{A}$		15.5	20	
RDS(ON)	Static Drain-Source On-Resistance	$V_{GS}=1.8\text{V}, I_D=2.5\text{A}$		20.5	35	
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1	μA
IGSS	Gate-Body Leakage Current	$V_{GS}=\pm 10\text{V}, V_{DS}=0\text{V}$			± 100	nA
C_{iss}	Input Capacitance	$V_{DS}=10\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		888		pF
C_{oss}	Output Capacitance			133		
C_{rss}	Reverse Transfer Capacitance			117		
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}, V_{DS}=10\text{V}, I_D=6.8\text{A}$		11.05		nC
Q_{gs}	Gate-Source Charge			1.73		
Q_{gd}	Gate-Drain Charge			3.1		
$t_{D(on)}$	Turn-on Delay Time	$V_{GS}=4.5\text{V}, V_{DS}=10\text{V}, I_D=6.8\text{A}$ $R_{GEN}=3\Omega$		7		ns
t_r	Turn-on Rise Time			46		
$t_{D(off)}$	Turn-off Delay Time			30		
t_f	Turn-off fall Time			52		
V_{SD}	Diode Forward Voltage	$I_S=7.6\text{A}, V_{GS}=0\text{V}$			1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

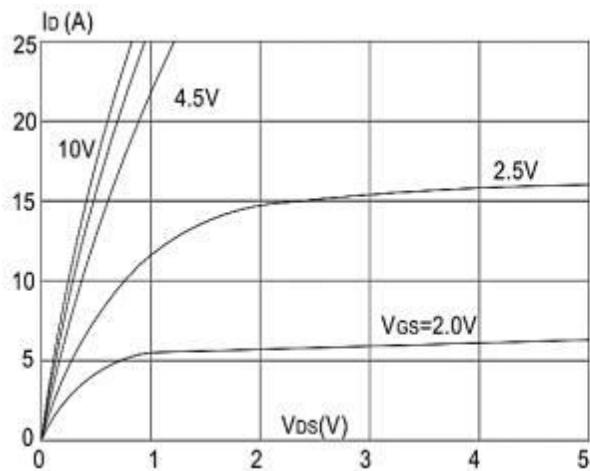


Figure 1: Output Characteristics

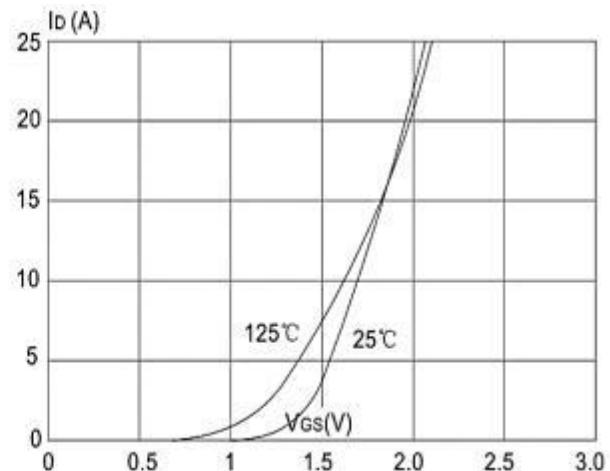


Figure 2: Typical Transfer Characteristics

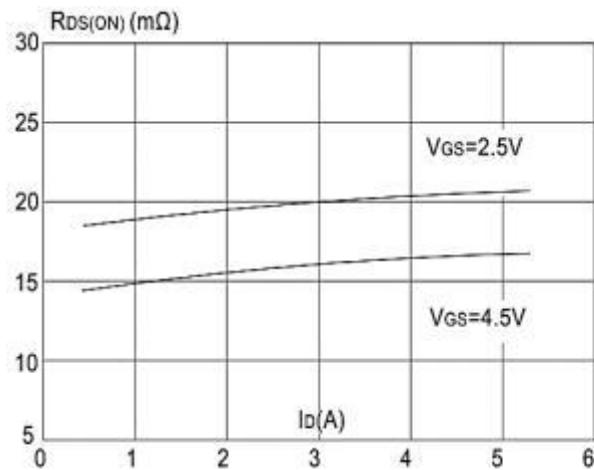


Figure 3: On-resistance vs. Drain Current

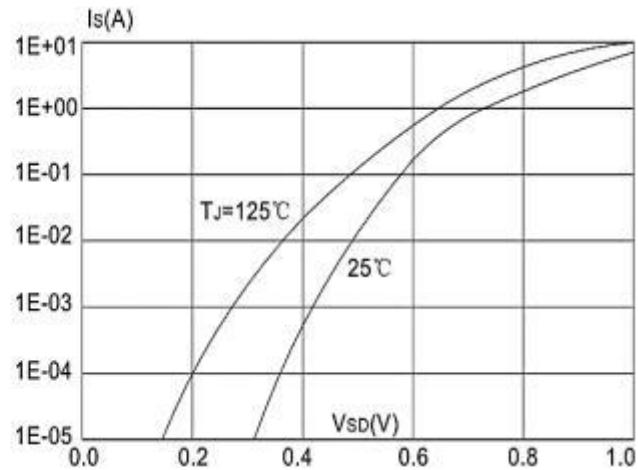


Figure 4: Body Diode Characteristics

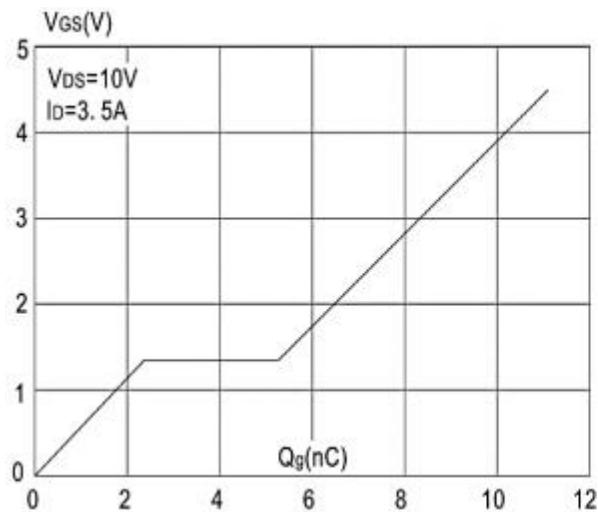


Figure 5: Gate Charge Characteristics

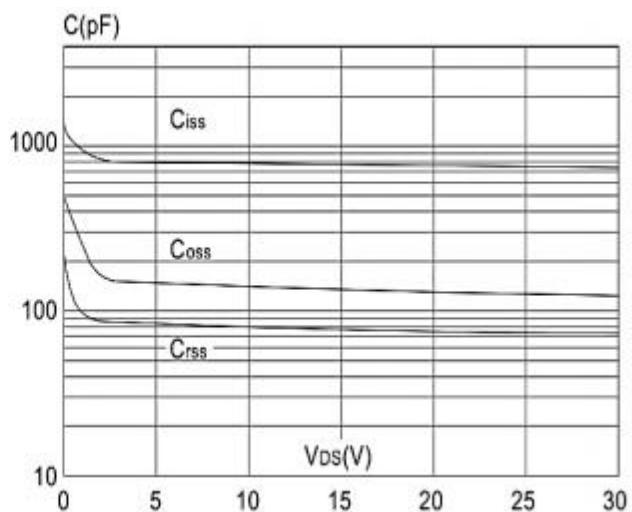


Figure 6: Capacitance Characteristics

Typical Characteristics

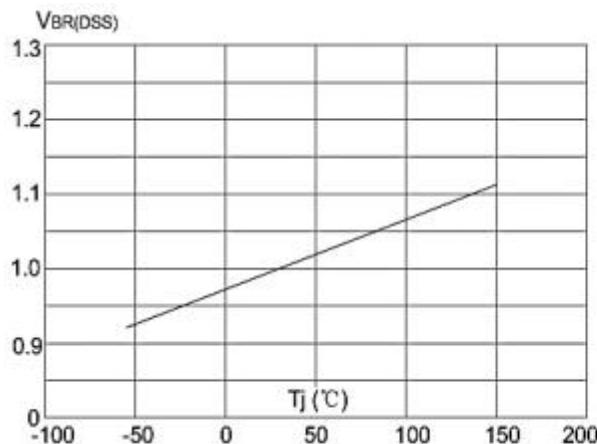


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

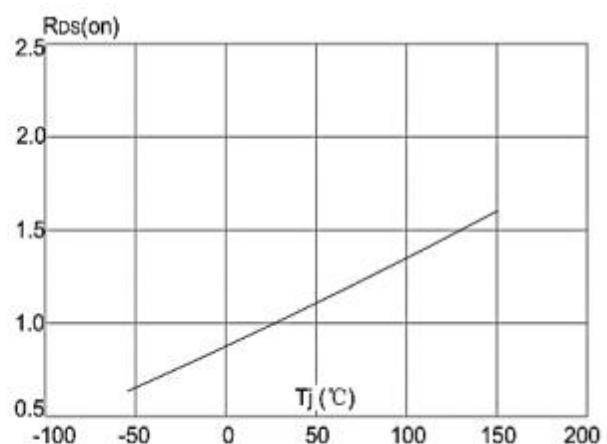


Figure 8: Normalized on Resistance vs. Junction Temperature

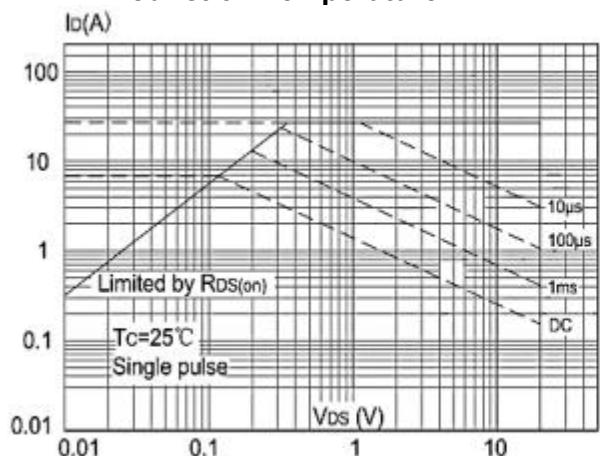


Figure 9: Maximum Safe Operating Area vs. Case Temperature

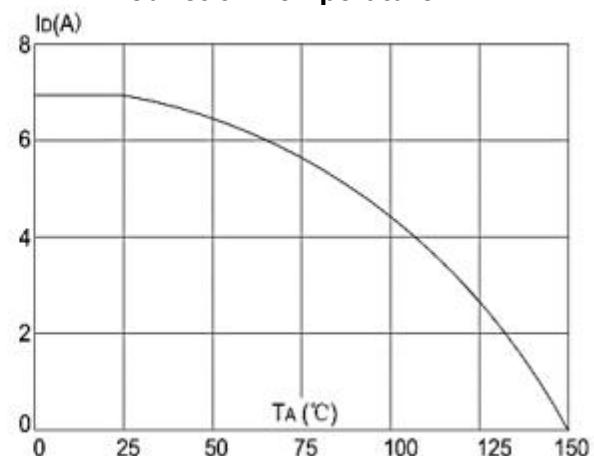


Figure 10: Maximum Continuous Drain Current

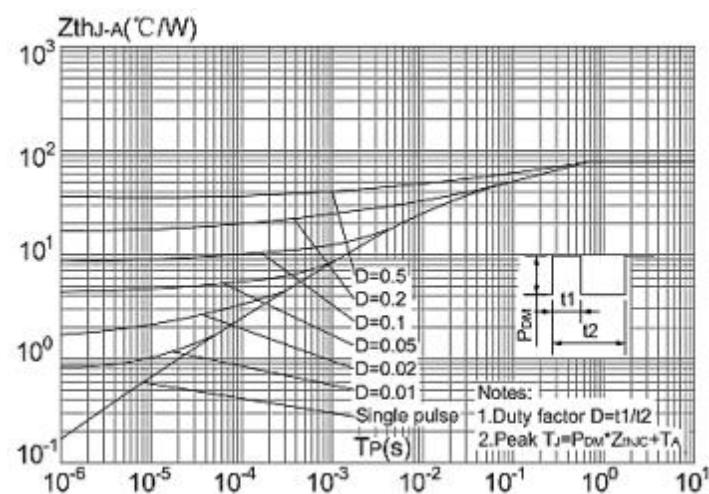
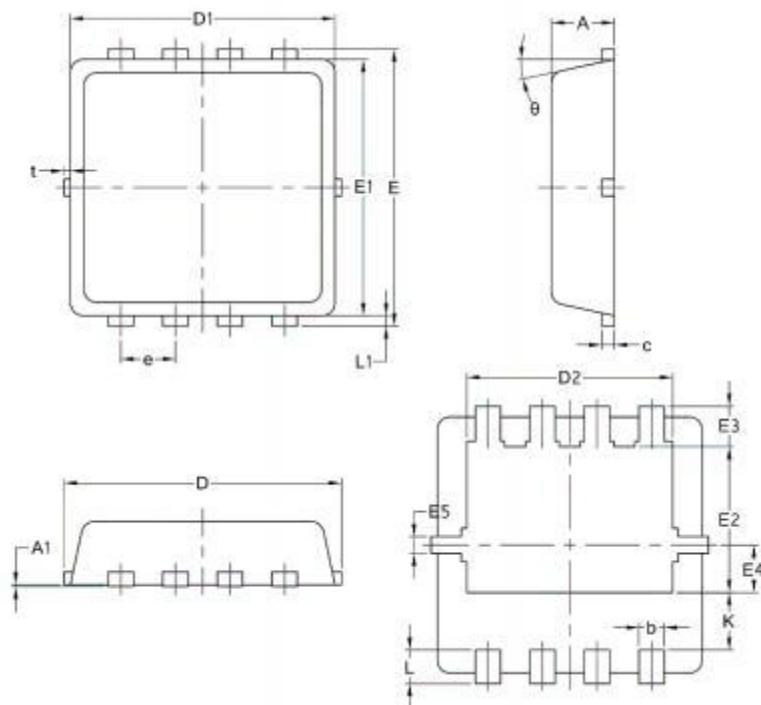


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Package Mechanical Data- PDFN3*3-8L-JQ Single



Symbol	Common mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN3X3-8L		5000